

**Silicon NPN Power Transistors**

**2SC2608**

**DESCRIPTION**

- With TO-3 package
- Complement to type 2SA1117
- High power dissipation

**APPLICATIONS**

- For power amplifier applications

**PINNING(see Fig.2)**

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

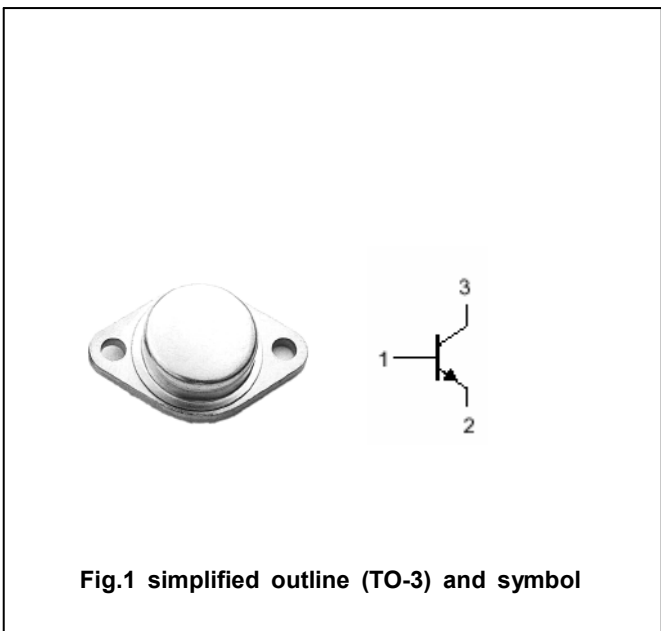


Fig.1 simplified outline (TO-3) and symbol

**ABSOLUTE MAXIMUM RATINGS( $T_c=25^\circ C$ )**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	200	V
$V_{CEO}$	Collector-emitter voltage	Open base	200	V
$V_{EBO}$	Emitter-base voltage	Open collector	6	V
$I_C$	Collector current		17	A
$P_C$	Collector power dissipation	$T_c=25^\circ C$	200	W
$T_j$	Junction temperature		150	$^\circ C$
$T_{stg}$	Storage temperature		-55~150	$^\circ C$

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## 2SC2608

## CHARACTERISTICS

T<sub>j</sub>=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =25mA ; I <sub>B</sub> =0	200			V
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =1mA ; I <sub>E</sub> =0	200			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =1mA ; I <sub>C</sub> =0	6			V
V <sub>CE(sat)</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =8A; I <sub>B</sub> =0.8A			2.0	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =200V; I <sub>E</sub> =0			0.1	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =6V; I <sub>C</sub> =0			0.1	mA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =8A ; V <sub>CE</sub> =4V	20			
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =1A ; V <sub>CE</sub> =12V		20		MHz

PACKAGE OUTLINE



Fig.2 outline dimensions (unindicated tolerance:±0.1mm)